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### U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
AA						
AB						
AC						
AD						
AE						

### FOREIGN PATENT DOCUMENTS

Examiner Initial	Document No.	Date	Country	Translation (Yes or No)
CAI	AF 11-251595	09/17/1999	Japan	Yes (Abstract Only), see page 2 in the spec.
CAI	AG 11-261063	09/24/1999	Japan	Yes (Abstract Only), see page 2 in the spec.
CAI	AH 2001-024187	01/26/2001	Japan	Yes (Abstract Only), see page 2 in the spec.
CAI	AI 2001-274379	10/05/2001	Japan	Yes (Abstract Only), see pages 2 and 52 in the spec.
CAI	AJ 10-125677	05/15/1998	Japan	Yes (Abstract Only)

### OTHER DOCUMENTS

CAI	AK	Murarka, S. P., "Silicides for VLSI Applications", Academic Press, Inc., pp. 88~95, 1983, (see pages 3 and 44 in the spec.)
CAI	AL	Qin M. et al., "Investigation of Polycrystalline Nickel Silicide films as a Gate Material", Journal of The Electrochemical Society, 148 (5) (The Electrochemical Society, Inc.), pp. G271~G274 (2001) (see pages 3 and 49 in the spec.)
Examiner		Date Considered 2/16/2005